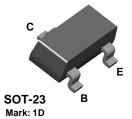


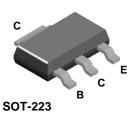
## MPSA42

# MMBTA42

# PZTA42







# **NPN High Voltage Amplifier**

This device is designed for application as a video output to drive color CRT and other high voltage applications. Sourced from Process 48.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	300	V
V <sub>CBO</sub>	Collector-Base Voltage	300	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.

  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic		Units		
		MPSA42	*MMBTA42	**PZTA42	
$P_D$	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

<sup>\*\*</sup> Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm $^2$ .

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## **NPN High Voltage Amplifier**

(continued)

Electri				

TA = 25°C unless otherwise noted

Parameter	Test Conditions	Min	Max	Units
RACTERISTICS				
Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	300		V
Collector-Base Breakdown Voltage	$I_C = 100  \mu A,  I_E = 0$	300		V
Emitter-Base Breakdown Voltage	$I_E = 100  \mu A,  I_C = 0$	6.0		V
Collector-Cutoff Current	$V_{CB} = 200 \text{ V}, I_{E} = 0$		0.1	μΑ
Emitter-Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_{C} = 0$		0.1	μΑ
	RACTERISTICS  Collector-Emitter Breakdown Voltage*  Collector-Base Breakdown Voltage  Emitter-Base Breakdown Voltage  Collector-Cutoff Current		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

### ON CHARACTERISTICS\*

h <sub>FE</sub>	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	25		
		$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 10 \text{ V}$	40		
		$I_C = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	40		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 20 \text{ mA}, I_B = 2.0 \text{ mA}$		0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 20 \text{ mA}, I_B = 2.0 \text{ mA}$		0.9	V

### SMALL SIGNAL CHARACTERISTICS

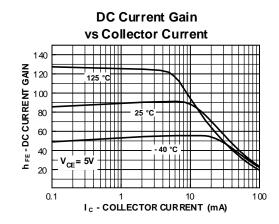
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	50		MHz
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		3.0	pF

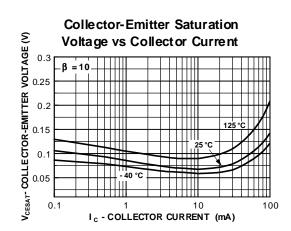
<sup>\*</sup>Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

## **Spice Model**

NPN (Is=34.9f Xti=3 Eg=1.11 Vaf=100 Bf=2.65K Ne=1.708 Ise=16.32p Ikf=23.79m Xtb=1.5 Br=9.769 Nc=2 Isc=0 Ikr=0 Rc=7 Cjc=14.23p Mjc=.5489 Vjc=.75 Fc=.5 Cje=49.62p Mje=.4136 Vje=.75 Tr=934.3p Tf=1.69n Itf=5 Vtf=20 Xtf=150 Rb=10)

## **Typical Characteristics**

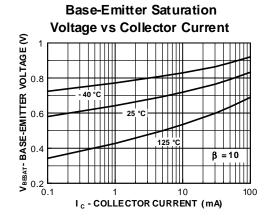


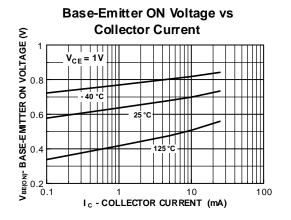


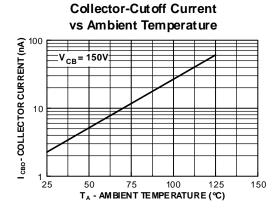
## **NPN High Voltage Amplifier**

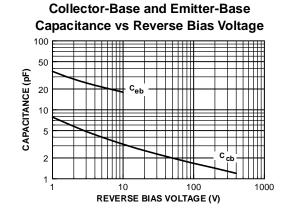
(continued)

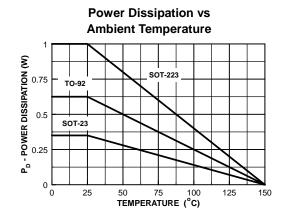
### Typical Characteristics (continued)

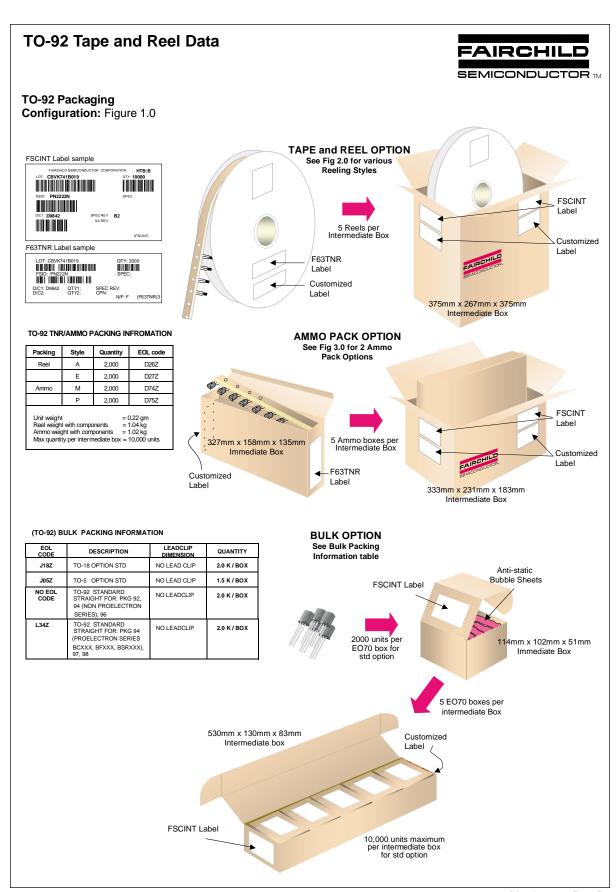










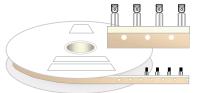


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## TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

### Machine Option "A" (H)



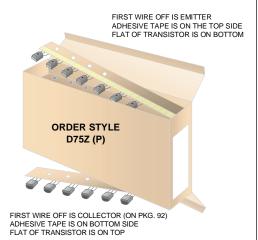
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

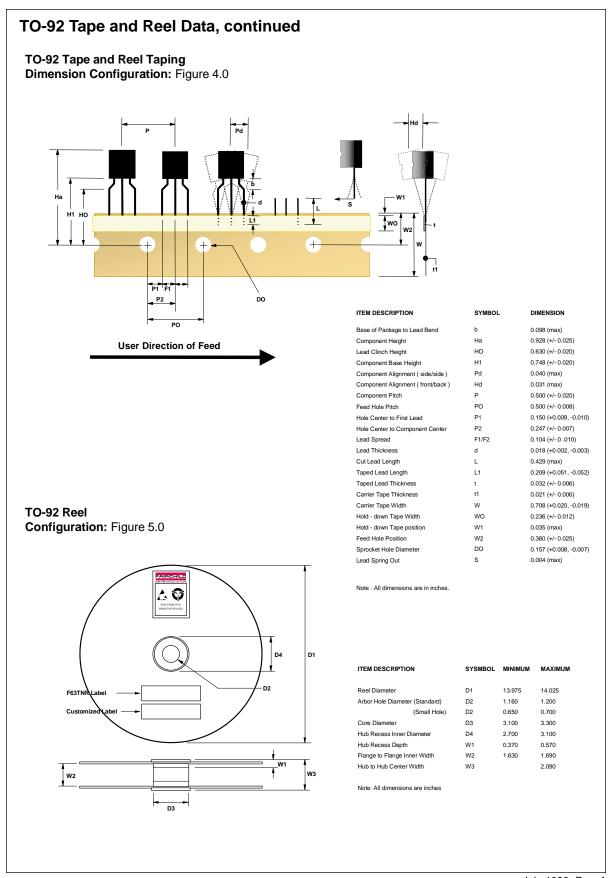
Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0





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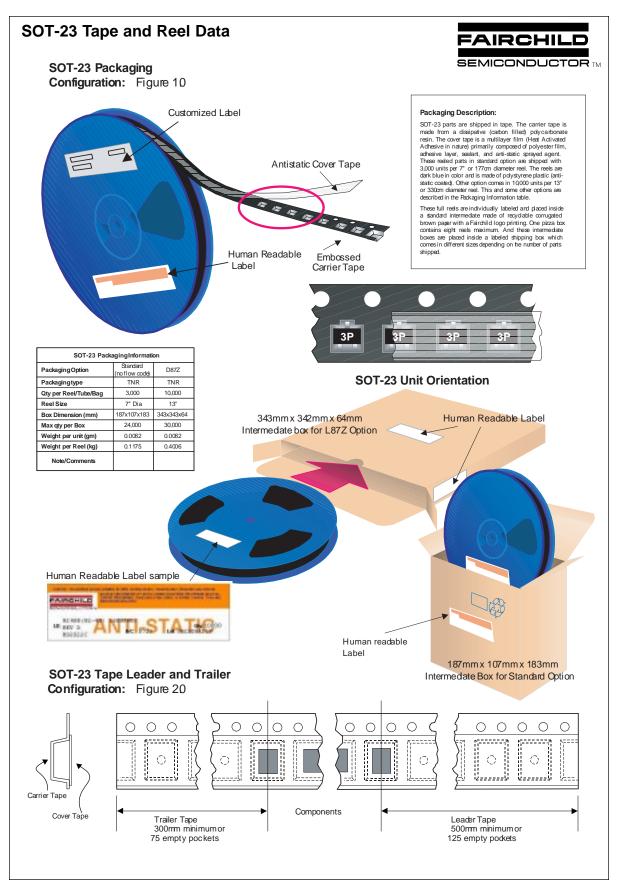


# **TO-92 Package Dimensions** FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

January 2000, Rev. B

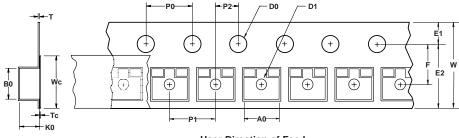


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## SOT-23 Tape and Reel Data, continued

### **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



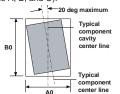
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



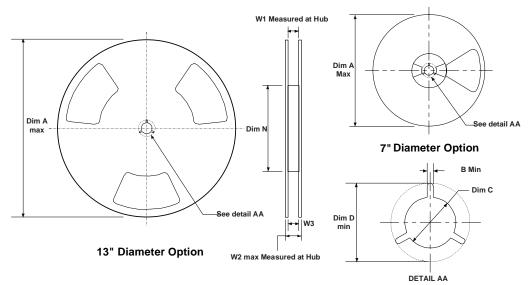
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

### SOT-23 Reel Configuration: Figure 4.0

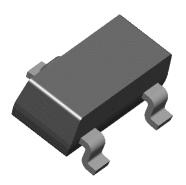


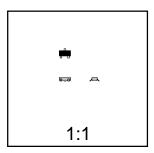
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

## **SOT-23 Package Dimensions**



# SOT-23 (FS PKG Code 49)

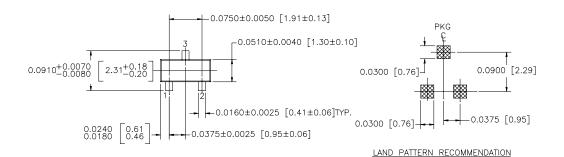


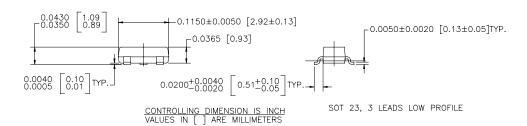


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082



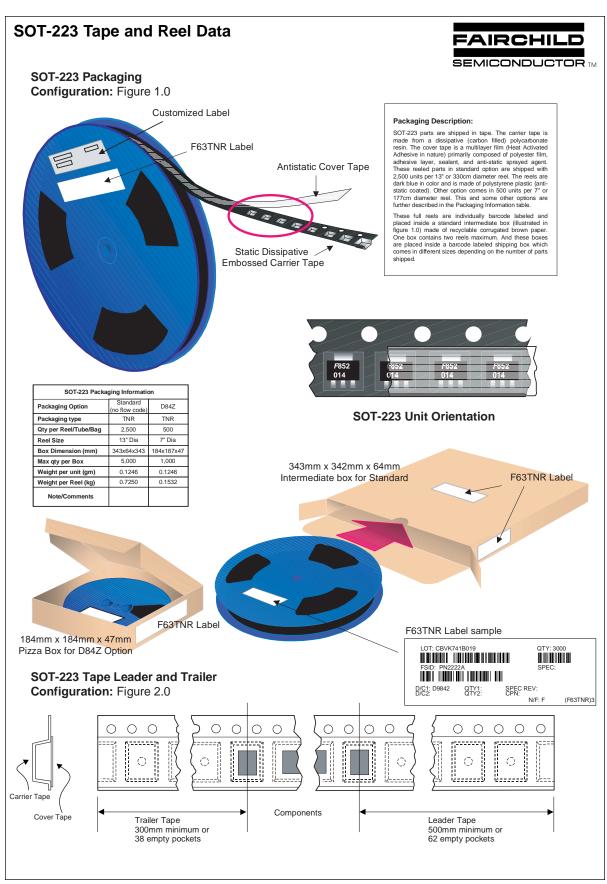


NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

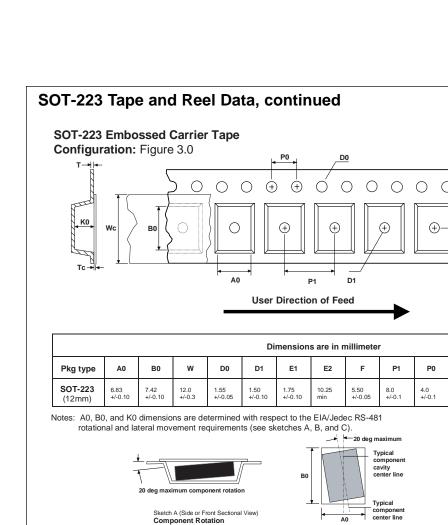
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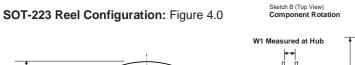
September 1998, Rev. A1

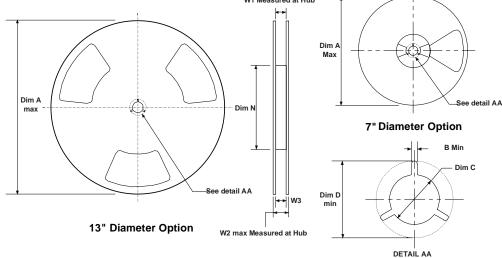


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K0

0.292 +/-0.0130 Wc

0.5mm maximum

Sketch C (Top View)

Component lateral movement

Tc

0.06 +/-0.02

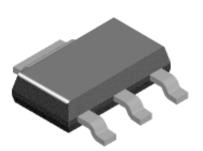
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

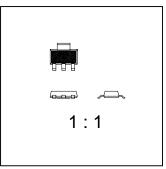
July 1999, Rev. B

## **SOT-223 Package Dimensions**



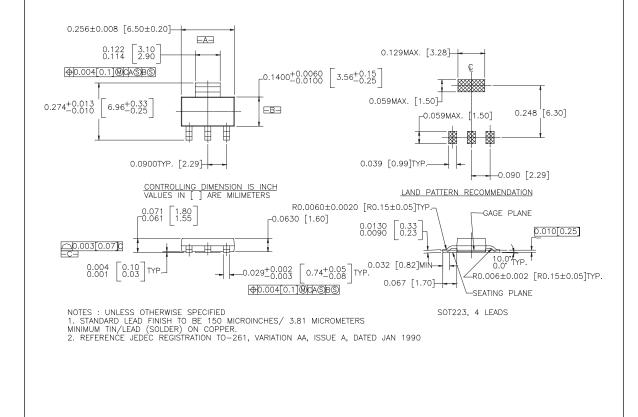
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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September 1999, Rev. C

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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Rev. G